DUAL P-CHANNEL MOSFET

–12 V, –4.0 A, 67 mΩ

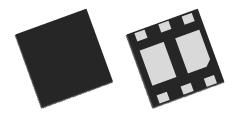
Description

The μ PA2672T1R is Dual P-channel MOS Field Effect Transistors for switching application.

This device features a low on-state resistance and excellent switching characteristics, and is suitable for applications such as power switch of portable machine and so on.

Features

- -1.8V drive available
- Low on-state resistance
 - ---- $R_{DS(on)1} = 67 \text{ m}\Omega \text{ MAX}. (V_{GS} = -4.5 \text{ V}, I_D = -2.0 \text{ A})$
 - ---- $R_{DS (on)2} = 92 \text{ m}\Omega \text{ MAX}. (V_{GS} = -2.5 \text{ V}, I_D = -2.0 \text{ A})$
 - ---- $R_{DS (on)3} = 159 \text{ m}\Omega \text{ MAX}. (V_{GS} = -1.8 \text{ V}, I_D = -2.0 \text{ A})$
- Built-in gate protection diode
- Lead-free and Halogen-free



6pinHUSON2020(Dual)

Ordering Information

Part Number	Package		
μPA2672T1R-E2-AX* ¹	6pinHUSON2020		

Note: *1. Pb-free (This product does not contain Pb in the external electrode and other parts.)

Absolute Maximum Ratings (T_A = 25°C)

ltem	Symbol	Ratings	Unit
Drain to Source Voltage ($V_{GS} = 0 V$)	V _{DSS}	-12	V
Gate to Source Voltage ($V_{DS} = 0 V$)	V _{GSS}	∓10	V
Drain Current (DC)	I _{D(DC)}	∓4.0	А
Drain Current (pulse) *1	I _{D(pulse)}	∓16	А
Total Power Dissipation (1 unit, 5 s) *2	P _{T1}	1.5	W
Total Power Dissipation (2 units, 5 s) *2	P _{T2}	2.3	W
Channel Temperature	T _{ch}	150	°C
Storage Temperature	T _{STG}	-55 to +150	°C

Notes: *1. PW \leq 10 μ s, Duty Cycle \leq 1%

*2. Mounted on glass epoxy board of 25.4mm x 25.4mm x 0.8mmt

R07DS0834EJ0101

Rev.1.01

Apr 15, 2013

Electrical Characteristics (T_A = 25°C)

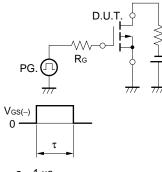
Characteristics	Symbol	MIN.	TYP.	MAX.	Unit	Test Conditions	
Zero Gate Voltage Drain Current	I _{DSS}			-1.0	μA	$V_{DS} = -12 \text{ V}, \text{ V}_{GS} = 0 \text{ V}$	
Gate Leakage Current	I _{GSS}			∓10	μA	V _{GS} = ∓8 V, V _{DS} = 0 V	
Gate Cut-off Voltage	V _{GS(off)}	-0.4		-1.1	V	$V_{DS} = -10 \text{ V}, I_D = -1 \text{ mA}$	
Forward Transfer Admittance *1	y _{fs}	4.5			S	$V_{DS} = -5 \text{ V}, \text{ I}_{D} = -2.0 \text{ A}$	
Drain to Source On-state	R _{DS(on)1}		52	67	mΩ	$V_{GS} = -4.5 \text{ V}, I_D = -2.0 \text{ A}$	
Resistance *1	R _{DS(on)2}		68	92	mΩ	$V_{GS} = -2.5 \text{ V}, I_D = -2.0 \text{ A}$	
	R _{DS(on)3}		95	159	mΩ	$V_{GS} = -1.8 \text{ V}, I_D = -2.0 \text{ A}$	
Input Capacitance	C _{iss}		486		pF	$V_{DS} = -10 \text{ V}, V_{GS} = 0 \text{ V},$	
Output Capacitance	C _{oss}		108		pF	f = 1.0 MHz	
Reverse Transfer Capacitance	C _{rss}		82		pF		
Turn-on Delay Time	t _{d (on)}		11.5		ns	$I_{D} = -2.0 \text{ A}, V_{DD} = -6 \text{ V}, \\ V_{GS} = -4.0 \text{ V}, R_{G} = 6 \Omega$	
Rise Time	tr		3.5		ns		
Turn-off Delay Time	t _{d (off)}		24.0		ns		
Fall Time	t _f		20.0		ns		
Total Gate Charge	Q _G		5.0		nC	$I_D = -4.0 \text{ A}$, $V_{DD} = -9.6 \text{ V}$,	
Gate to Source Charge	Q _{GS}		1.0		nC	V _{GS} = -4.5 V	
Gate to Drain Charge	Q _{GD}		1.3		nC	1	
Body Diode Forward Voltage *1	V _{F(S-D)}			1.5	V	$I_F = 4.0 \text{ A}, V_{GS} = 0 \text{ V}$	

Note: *1. Pulsed

TEST CIRCUIT 1 SWITCHING TIME

R

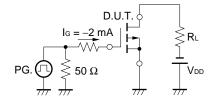
Vdd



 $\tau = 1 \ \mu s$ Duty Cycle $\leq 1\%$

Vgs(-) VGS Wave Form 0 10% 90% Vgs VDS(-) 90% 90% Vds V_{DS} Wave Form 10% 10% 0 tr tf td(on) td(off) tor tof

TEST CIRCUIT 2 GATE CHARGE



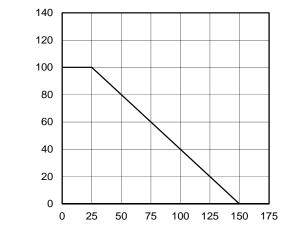


dT - Percentage of Rated Power - %

I_D – Drain Current - A

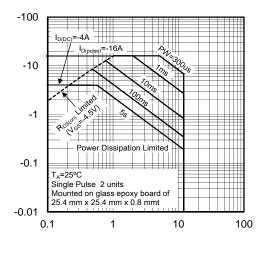
Typical Characteristics ($T_A = 25^{\circ}C$)

DERATING FACTOR OF FORWARD BIAS SAFE OPERATING AREA

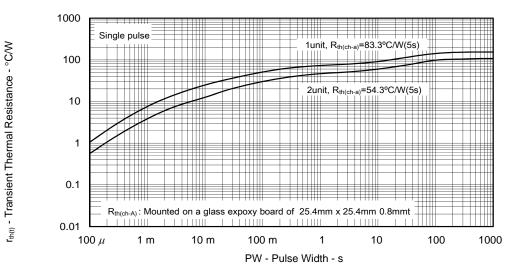


T_A -Ambient Temperature - °C



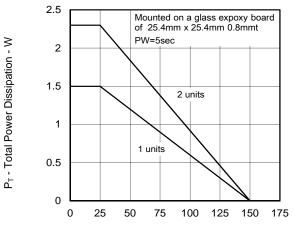


 V_{DS} - Drain to Source Voltage - V



TRANSIENT THERMAL RESISTANCE vs. PULSE WIDTH

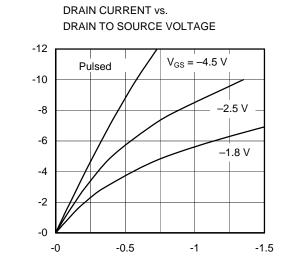
TOTAL POWER DISSIPATION vs. AMBIENT TEMPERATURE



T_A -Ambient Temperature - °C

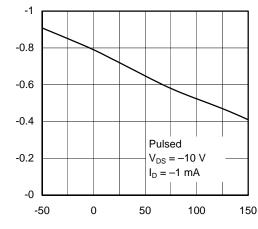
I_D –Drain Current - A

V_{GS(off)} – Gate to Source Cut-off Voltage - V





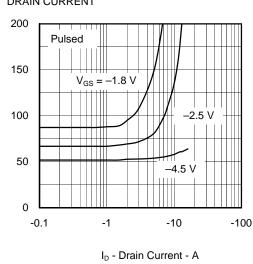
GATE TO SOURCE CUT-OFF VOLTAGE vs. CHANNEL TEMPERATURE



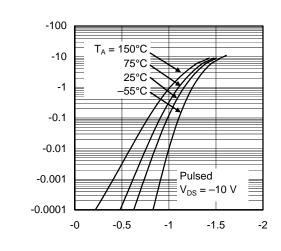
 T_{ch} - Channel Temperature - $^{\circ}C$

DRAIN TO SOURCE ON-STATE RESISTANCE vs. DRAIN CURRENT





FORWARD TRANSFER CHARACTERISTICS

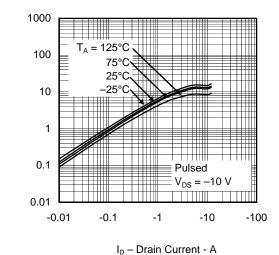


Ip - Drain Current - A

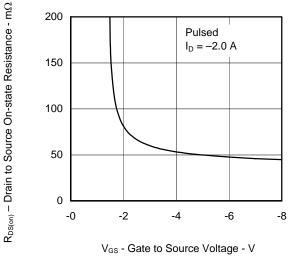
 $\mid y_{\rm fs} \mid$ - Forward Transfer Admittance - S

 V_{GS} - Gate to Source Voltage - V

FORWARD TRANSFER ADMITTANCE vs. DRAIN CURRENT



DRAIN TO SOURCE ON-STATE RESISTANCE vs. GATE TO SOURCE VOLTAGE



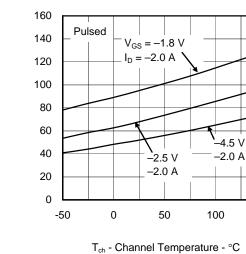
то

R07DS0834EJ0101 Rev.1.01 Apr 15, 2013 $R_{\text{DS(on)}}$ –Drain to Source On-state Resistance - $m\Omega$

t_{d(on)}, t_i, t_{d(off)}, t_r - Switching Time - *µs*

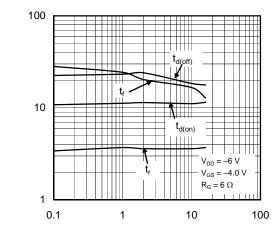
I_F - Diode Forward Current – A

DRAIN TO SOURCE ON-STATE RESISTANCE vs. CHANNEL TEMPERATURE



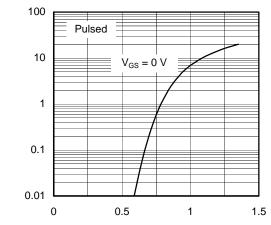
SWITCHING CHARACTERISTICS

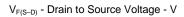
150



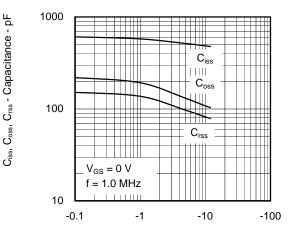
I_D - Drain Current - A

SOURCE TO DRAIN DIODE FORWARD VOLTAGE



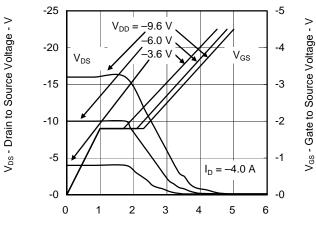


CAPACITANCE vs. DRAIN TO SOURCE VOLTAGE



V_{DS} – Drain to Source Voltage - V

DYNAMIC INPUT/OUTPUT CHARACTERISTICS

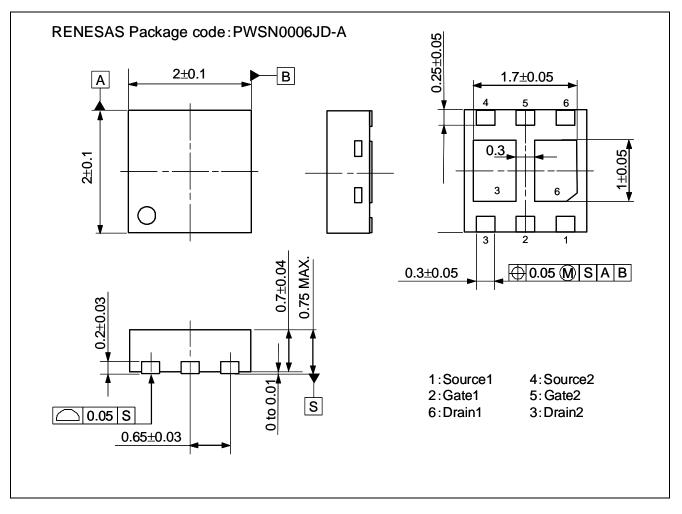


Q_G - Gate Charge - nC

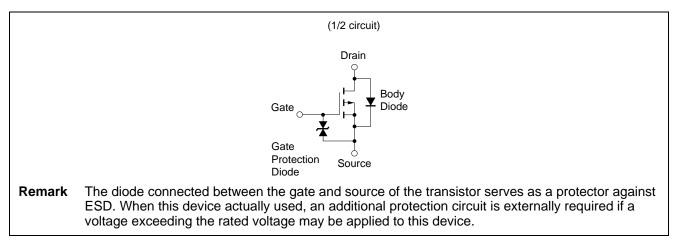


Package Drawings (Unit: mm)

6pinHUSON2020



Equivalent Circuit



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Renesas Electronics Corporation

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 Renesas Electronics America Inc.

 2880 Scott Boulevard Santa Clara, CA 95050-2554, U.S.A.

 Tel: +1-408-588-6000, Fax: +1-408-588-6130

 Renesas Electronics Canada Limited

 1011 Nicholson Road, Newmarket, Ontario L3Y 9C3, Canada

 Tel: +1-408-989-5441, Fax: +1-905-898-3220

 Renesas Electronics Europe Limited

 Dukes Meadow, Millboard Road, Bourne End, Buckinghamshire, SL8 5FH, U.K

 Tel: +44-1628-651-700, Fax: +44-1628-651-804

 Renesas Electronics Europe GmbH

 Arcadiastrasse 10, 40472 Dusseldorf, Germany

 Tel: +49-211-65030, Fax: +44-11628-651-804

 Renesas Electronics China) Co., Ltd.

 The Floor, Quantum Plaza, No. 27 ZhiChunLu Haidian District, Beijing 100083, P.R.China

 Tel: +86-10-6235-1155, Fax: +865-10-6235-7679

 Renesas Electronics (Shanghal) Co., Ltd.

 Unit 204, 205, AZIA Center, No.1233 Luijazu Ring Fd., Pudong District, Shanghai 200120, China

 Tel: +862-78587-71818, Fax: +865-21687-7858

 Renesas Electronics Hong Kong Limited

 Unit 1601-1613, 16/F., Tower 2, Grand Century Place, 193 Prince Edward Road West, Mongkok, Kowloon, Hong Kong

 Tel: +862-48175-9800, Fax: +865 2886-9022/9044

 Renesas Electronics Taiwan Co., Ltd.

 137. No. 383, Fu Shing Noth Road, Taipei, Taiwan

 Tel: +652-785900, Fax: +865 2-867759

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